

### Vishay Semiconductors

# Fast Infrared Transceiver Module (FIR, 4 Mbit/s) for 2.4 V to 5.5 V Operation





#### **DESCRIPTION**

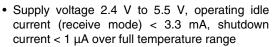
The TFDU6103 is a low-power infrared transceiver module compliant to the latest IrDA® physical layer standard for fast infrared data communication, supporting IrDA speeds up to 4 Mbit/s (FIR), and carrier based remote control modes up to 2 MHz. Integrated within the transceiver module are a PIN photodiode, an infrared emitter (IRED), and a low-power CMOS control IC to provide a total front-end solution in a single package.

Vishay FIR transceivers are available in different package options, including this BabyFace package (TFDU6103). This wide selection provides flexibility for a variety of applications and space constraints. The transceivers are capable of directly interfacing with a wide variety of I/O devices which perform the modulation/demodulation function, including National Semiconductor's PC87338, PC87108 and PC87109, SMC's FDC37C669, FDC37N769 and CAM35C44, and Hitachi's SH3. TFDU6103 has a tri-state output and is floating in shut-down mode with a weak pull-up.

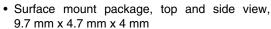
#### **APPLICATIONS**

- Notebook computers, desktop PCs, palmtop computers (Win CE, Palm PC), PDAs
- · Digital still and video cameras
- · Printers, fax machines, photocopiers, screen projectors
- Telecommunication products (cellular phones, pagers)
- Internet TV boxes, video conferencing systems
- External infrared adapters (dongles)
- · Medical an industrial data collection

#### **FEATURES**







(e3)

COMPLIANT

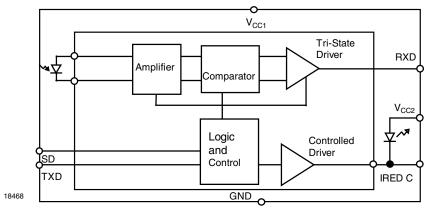
- Operating temperature 25 °C to 85 °C
- Transmitter wavelength typ. 886 nm, supporting IrDA and remote control
- IrDA compliant, link distance > 1 m, ± 15°, window losses are allowed to still be inside the IrDA spec.
- Remote control range > 8 m, typ. 22 m
- ESD > 1 kV
- Latchup > 100 mA
- EMI immunity > 550 V/m for GSM frequency and other mobile telephone bands/(700 MHz to 2000 MHz, no external shield)
- Split power supply, LED can be driven by a separate power supply not loading the regulated supply. U.S. pat. no. 6,157,476
- Tri-state-receiver output, floating in shut down with a weak pull-up
- Eye safety class 1 (IEC 60825-1, ed. 2001), limited LED on-time, LED current is controlled, no single fault to be considered
- Qualified for lead (Pb)-free and Sn/Pb processing (MSL4)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

PRODUCT SUMMARY								
PART NUMBER	DATA RATE (kbit/s)	DIMENSIONS HxLxW (mmxmmxmm)  LINK DISTANCE (m)		OPERATING VOLTAGE (V)	IDLE SUPPLY CURRENT (mA)			
TFDU6103	4000	4 x 9.7 x 4.7	0 to ≥ 1	2.4 to 5.5	2			

PARTS TABLE						
PART	DESCRIPTION	QTY/REEL				
TFDU6103-TR3	Oriented in carrier tape for side view surface mounting	1000 pcs				
TFDU6103-TT3	Oriented in carrier tape for top view surface mounting	1000 pcs				



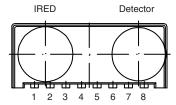
#### **FUNCTIONAL BLOCK DIAGRAM**



#### **PINOUT**

TFDU6103 weight 0.2 g

"U" Option Baby Face (universal)



17087

#### **Definitions:**

In the Vishay transceiver datasheets the following nomenclature is used for defining the IrDA operating modes: SIR: 2.4 kbit/s to 115.2 kbit/s, equivalent to the basic serial infrared standard with the physical layer version IrPhy 1.0

MIR: 576 kbit/s to 1152 kbit/s

FIR: 4 Mbit/s VFIR: 16 Mbit/s

MIR and FIR were implemented with IrPhy 1.1, followed by IrPhy 1.2, adding the SIR low power standard. IrPhy 1.3 extended the low power option to MIR and FIR and VFIR was added with IrPhy 1.4. A new version of the standard in any case obsoletes the former version.

#### Note

We apologize to use sometimes in our documentation the abbreviation LED and the word light emitting diode instead of infrared emitting diode (IRED) for IR-emitters. That is by definition wrong; we are here following just a bad trend.

Typical values are for design aid only, not guaranteed nor subject to production testing and may vary with time.

PIN DES	CRIPTIO	N		
PIN NUMBER SYMBOL		DESCRIPTION	I/O	ACTIVE
1	V <sub>CC2</sub> IRED anode	Connect IRED anode directly to V <sub>CC2</sub> . For voltages higher than 3.6 V an external resistor might be necessary for reducing the internal power dissipation.  An unregulated separate power supply can be used at this pin		
2	2 IRED cathode, internally connected to driver transistor			
3	TXD	This input is used to transmit serial data when SD is low. An on-chip protection circuit disables the LED driver if the TXD pin is asserted for longer than 100 µs. When used in conjunction with the SD pin, this pin is also used to set receiver speed mode	I	High
4	RXD	Received data output, push-pull CMOS driver output capable of driving a standard CMOS or TTL load. No external pull-up or pull-down resistor is required.  Floating with a weak pull-up of 500 kΩ (typ.) in shutdown mode	0	Low
5	SD	Shutdown, also used for dynamic mode switching. Setting this pin active places the module into shutdown mode. On the falling edge of this signal, the state of the TXD pin is sampled and used to set receiver low bandwidth (TXD = low, SIR) or high bandwidth (TXD = high, MIR and FIR) mode	I	High
6	V <sub>CC1</sub>	Supply voltage		
7	NC			
8	GND	Ground		



PARAMETER	TEST CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply voltage range, transceiver	0 V < V <sub>CC2</sub> < 6 V	V <sub>CC1</sub>	- 0.5		+ 6	V
Supply voltage range, transmitter	0 V < V <sub>CC1</sub> < 6 V	V <sub>CC2</sub>	- 0.5		+ 6.5	V
Input currents	For all pins, except IRED anode pin				10	mA
Output sinking current					25	mA
Power dissipation	See derating curve, figure 6	P <sub>D</sub>			500	mW
Junction temperature		TJ			125	°C
Ambient temperature range (operating)		T <sub>amb</sub>	- 25		+ 85	°C
Storage temperature range		T <sub>stg</sub>	- 25		+ 85	°C
Soldering temperature	See recommended solder profile (see figure 4)				260	°C
Average output current		I <sub>IRED</sub> (DC)			125	mA
Repetitive pulse output current	< 90 μs, t <sub>on</sub> < 20 %	I <sub>IRED</sub> (RP)			600	mA
IRED anode voltage		V <sub>IREDA</sub>	- 0.5		+ 6.5	V
Voltage at all inputs and outputs	V <sub>IN</sub> > V <sub>CC1</sub> is allowed	V <sub>IN</sub>			5.5	V

#### Note

Reference point ground pin 8, unless otherwise noted.

Typical values are for design aid only, not guaranteed nor subject to production testing and may vary with time.

EYE SAFETY INFORMATION					
STANDARD	CLASSIFICATION				
IEC/EN 60825-1 (2007-03), DIN EN 60825-1 (2008-05) "SAFETY OF LASER PRODUCTS - Part 1: equipment classification and requirements", simplified method	Class 1				
IEC 62471 (2006), CIE S009 (2002) "Photobiological Safety of Lamps and Lamp Systems"	Exempt				
DIRECTIVE 2006/25/EC OF THE EUROPEAN PARLIAMENT AND OF THE COUNCIL of 5 <sup>th</sup> April 2006 on the minimum health and safety requirements regarding the exposure of workers to risks arising from physical agents (artificial optical radiation) (19 <sup>th</sup> individual directive within the meaning of article 16(1) of directive 89/391/EEC)	Exempt				

#### Note

Vishay transceivers operating inside the absolute maximum ratings are classified as eye safe according the above table.

ELECTRICAL CHARACTERISTICS (1)								
PARAMETER	TEST CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
TRANSCEIVER	•							
Supply voltage		V <sub>CC</sub>	2.4		5.5	V		
Dynamic supply current	Receive mode only, idle In transmit mode, add additional 85 mA (typ.) for IRED current. Add RXD output current depending on RXD load.							
	SIR mode	Icc		1.8	3	mA		
	MIR/FIR mode	Icc		2	3.3	mA		
Shutdown supply current	SD = high T = 25 °C, not ambient light sensitive, detector is disabled in shutdown mode	I <sub>SD</sub>		0.01		μΑ		
.,,	SD = high, full specified temperature range, not ambient light sensitive	I <sub>SD</sub>			1	μΑ		
Operating temperature range		T <sub>A</sub>	- 25		+ 85	°C		
Input voltage low (TXD, SD)		V <sub>IL</sub>	- 0.5		0.5	V		

### **TFDU6103**



### Vishay Semiconductors Fast Infrared Transceiver Module (FIR, 4 Mbit/s) for 2.4 V to 5.5 V Operation

ELECTRICAL CHARAC	ELECTRICAL CHARACTERISTICS (1)								
PARAMETER	TEST CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
TRANSCEIVER									
Input voltage high (TXD, SD)	CMOS level (2)	V <sub>IH</sub>	V <sub>CC</sub> - 0.3		6	V			
Input leakage current (TXD, SD)	V <sub>IN</sub> = 0.9 x V <sub>CC1</sub>	I <sub>ICH</sub>	- 1		+ 1	μА			
Input capacitance, TXD, SD		C <sub>I</sub>			5	pF			
Output voltage low	$I_{OL} = 500 \mu A, C_{load} = 15 pF$	V <sub>OL</sub>			0.4	V			
Output voltage high	$I_{OH} = 250 \mu A, C_{load} = 15 pF$	V <sub>OH</sub>	0.9 x V <sub>CC1</sub>			V			
Output RXD current limitation high state low state	Short to ground Short to V <sub>CC1</sub>				20 20	mA mA			
SD shutdown pulse duration	Activating shutdown		30		∞	μs			
RXD to V <sub>CC1</sub> impedance		R <sub>RXD</sub>	400	500	600	kΩ			
SD mode programming pulse duration	All modes	t <sub>SDPW</sub>	200			ns			

#### Note

 (1) T<sub>amb</sub> = 25 °C, V<sub>CC1</sub> = V<sub>CC2</sub> = 2.4 V to 5.5 V unless otherwise noted. Typical values are for design aid only, not guaranteed nor subject to production testing.
 (2) The typical threshold level is 0.5 x V<sub>CC1</sub> (V<sub>CC1</sub> = 3 V). It is recommended to use the specified min./max. values to avoid increased operating current.

OPTOELECTRONIC C	HARACTERISTICS (1)					
PARAMETER	TEST CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
RECEIVER						
Minimum irradiance E <sub>e</sub> in angular range <sup>(3)</sup> SIR mode	9.6 kbit/s to 115.2 kbit/s $\lambda$ = 850 nm to 900 nm	E <sub>e</sub>		25 (2.5)	35 (3.5)	mW/m <sup>2</sup> (μW/cm <sup>2</sup> )
Minimum irradiance E <sub>e</sub> in angular range, MIR mode	1.152 Mbit/s $\lambda$ = 850 nm to 900 nm	E <sub>e</sub>		65 (6.5)		mW/m <sup>2</sup> (μW/cm <sup>2</sup> )
Minimum irradiance E <sub>e</sub> inangular range, FIR mode	4 Mbit/s $\lambda$ = 850 nm to 900 nm	E <sub>e</sub>		80 (8)	90 (9)	mW/m <sup>2</sup> (μW/cm <sup>2</sup> )
Maximum irradiance E <sub>e</sub> in angular range <sup>(4)</sup>	λ = 850 nm to 900 nm	E <sub>e</sub>		5 (500)		kW/m <sup>2</sup> (mW/cm <sup>2</sup> )
Maximum no detection irradiance	(2)	E <sub>e</sub>	4 (0.4)			mW/m <sup>2</sup> (μW/cm <sup>2</sup> )
Rise time of output signal	10 % to 90 %, 15 pF	t <sub>r (RXD)</sub>	10		40	ns
Fall time of output signal	90 % to 10 %, 15 pF	t <sub>f (RXD)</sub>	10		40	ns
RXD pulse width of output	Input pulse length, 1.4 $\mu s < P_{Wopt} < 25 \ \mu s$	t <sub>PW</sub>		2.1		μs
signal, 50 %, SIR mode	Input pulse length, 1.4 $\mu s < P_{Wopt} < 25 \ \mu s,$ - 25 °C < T < 85 °C $^{(5)}$	t <sub>PW</sub>	1.5	1.8	2.6	μs
RXD pulse width of output signal, 50 %, MIR mode	Input pulse length, P <sub>Wopt</sub> = 217 ns, 1.152 Mbit/s	t <sub>PW</sub>	110	250	270	ns
RXD pulse width of output	Input pulse length, P <sub>Wopt</sub> = 125 ns, 4 Mbit/s	t <sub>PW</sub>	100		140	ns
signal, 50 %, FIR mode	Input pulse length, P <sub>Wopt</sub> = 250 ns, 4 Mbit/s	t <sub>PW</sub>	225		275	ns
	Input irradiance = 100 mW/m <sup>2</sup> , 4 Mbit/s				20	ns
	Input irradiance = 100 mW/m <sup>2</sup> , 1.152 Mbit/s				40	ns
otoonastic jitter, reading edge	Input irradiance = 100 mW/m <sup>2</sup> , 576 kbit/s				80	ns
	Input irradiance = 100 mW/m $^2$ , $\leq$ 115.2 kbit/s				350	ns
Receiver start up time	After completion of shutdown programming sequence power on delay				250	μs
Latency		t∟		40	100	μs



PARAMETER	TEST CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
TRANSMITTER			•	•		
IRED operating current, switched current limiter	Note: no external current limiting resistor is needed for $V_{CC1} = V_{CC2} = 3.3 \text{ V}$	I <sub>D</sub>	330	440	600	mA
	Input pulse width t < 20 μs	t <sub>pw</sub>		t		μs
Output pulse width limitation	Input pulse width 20 μs < t < 150 μs	t <sub>pw</sub>	18		150	μs
	Input pulse width t ≥ 150 μs	t <sub>pw_lim</sub>			150	μs
Output leakage IRED current		I <sub>IRED</sub>	- 1		1	μΑ
Output radiant intensity, see figure 1, recommended application circuit	$V_{CC} = V_{IRED} = 3.3 \text{ V}, \ \alpha = 0^{\circ}$ TXD = high, SD = low, R1 = 1 $\Omega$	l <sub>e</sub>	110	170	468 <sup>(6)</sup>	mW/sr
Output radiant intensity, see figure 1, recommended application circuit	$V_{CC} = V_{IRED} = 3.3 \text{ V}, \ \alpha = 0^{\circ}, \ 15^{\circ}$ TXD = high, SD = low, R1 = 1 $\Omega$	l <sub>e</sub>	100	130	468 <sup>(6)</sup>	mW/sr
Output radiant intensity	$V_{CC1}=3.3~V,~\alpha=0^{\circ},~15^{\circ}$ TXD = low or SD = high (receiver is inactive as long as SD = high)	l <sub>e</sub>			0.04	mW/sr
Output radiant intensity, angle of half intensity		α		± 24		deg
Peak - emission wavelength (7)		λρ	875	886	900	nm
Spectral bandwidth		Δλ		45		nm
Optical rise time, Optical fall time		t <sub>ropt</sub> , t <sub>fopt</sub>	10		40	ns
	Input pulse width 217 ns, 1.152 Mbit/s	t <sub>opt</sub>	207	217	227	ns
Optical output pulse duration	Input pulse width 125 ns, 4 Mbit/s	t <sub>opt</sub>	117	125	133	ns
	Input pulse width 250 ns, 4 Mbit/s	t <sub>opt</sub>	242	250	258	ns
Optical overshoot		-			25	%

#### **Notes**

- (1) T<sub>amb</sub> = 25 °C, V<sub>CC</sub> = 2.4 V to 5.5 V unless otherwise noted. All timing data measured with 4 Mbit/s are measured using the IrDA FIR transmission header. The data given here are valid 5 μs after starting the preamble. Typical values are for design aid only, not guaranteed nor subject to production testing.
- (2) This parameter reflects the backlight test of the IrDA physical layer specification to guarantee immunity against light from fluorescent lamps.
- (3) IrDA sensitivity definition: minimum irradiance E<sub>e</sub> in angular range, power per unit area. The receiver must meet the BER specification while the source is operating at the minimum intensity in angular range into the minimum half-angular range at the maximum link length.
- (4) Maximum irradiance E<sub>e</sub> in angular range, power per unit area. The optical delivered to the detector by a source operating at the maximum intensity in angular range at minimum link length must not cause receiver overdrive distortion and possible related link errors. If placed at the active output interface reference plane of the transmitter, the receiver must meet its bit error ratio (BER) specification. For more definitions see the document "Symbols and Terminology" on the Vishay website
- (5) Retriggering once during applied optical pulse may occur.
- (6) Maximum value is given by eye safety class 1, IEC 60825-1, simplified method.
- (7) Due to this wavelength restriction compared to the IrDA spec of 850 nm to 900 nm the transmitter is able to operate as source for the standard remote control applications with codes as e.g. Philips RC5/RC6® or RECS 80. When operated under IrDA full range conditions (125 mW/sr) the RC range to be covered is in the range from 8 m to 12 m, provided that state of the art remote control receivers are used.



#### RECOMMENDED CIRCUIT DIAGRAM

Vishay Semiconductors transceivers integrate a sensitive receiver and a built-in power driver. The combination of both needs a careful circuit board layout. The use of thin, long, resistive and inductive wiring should be avoided. The inputs (TXD, SD) and the output RXD should be directly (DC) coupled to the I/O circuit.

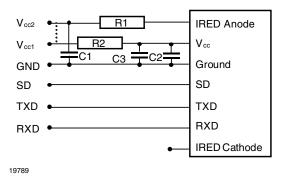


Fig. 1 - Recommended Application Circuit

The capacitor C1 is buffering the supply voltage and reduces the influence of the inductance of the power supply line. This one should be a Tantalum or other fast capacitor to guarantee the fast rise time of the IRED current. The resistor R1 is only necessary for higher operating voltages and elevated temperatures, see derating curve in figure 6, to avoid too high internal power dissipation.

The capacitors C2 and C3 combined with the resistor R2 (as the low pass filter) is smoothing the supply voltage  $V_{CC1}$ . R2, C1, C2, and C3 are optional and dependent on the quality of the supply voltages  $V_{CC1}$  and  $V_{CC2}$  and injected noise. An unstable power supply with dropping voltage during transmission may reduce sensitivity (and transmission range) of the transceiver. The placement of these parts is critical. It is strongly recommended to position C2 and C3 as close as possible to the transceiver power supply pins. An tantalum capacitor should be used for C1 and C3 while a ceramic capacitor is used for C2.

In addition, when connecting the described circuit to the power supply, low impedance wiring should be used.

When extended wiring is used the inductance of the power supply can cause dynamically a voltage drop at  $V_{CC2}$ . Often some power supplies are not able to follow the fast current rise time. In that case another 4.7  $\mu$ F (type, see table under C1) at  $V_{CC2}$  will be helpful.

Keep in mind that basic RF-design rules for circuit design should be taken into account. Especially longer signal lines should not be used without termination. See e.g. "The Art of Electronics" Paul Horowitz, Wienfield Hill, 1989, Cambridge University Press, ISBN: 0521370957.

TABLE 1 - F	TABLE 1 - RECOMMENDED APPLICATION CIRCUIT COMPONENTS							
COMPONENT RECOMMENDED VALUE VISHAY PART NUMBER								
C1, C3	4.7 μF, 16 V	293D 475X9 016B						
C2	0.1 μF, ceramic	VJ 1206 Y 104 J XXMT						
R1	3.3 V supply voltage: no resistors necessary, the internal controller is able to control the current	e.g. 2 x CRCW-1206-1R0-F-RT1						
R2	10 Ω, 0.125 W	CRCW-1206-10R0-F-RT1						

#### I/O AND SOFTWARE

In the description, already different I/Os are mentioned. Different combinations are tested and the function verified with the special drivers available from the I/O suppliers. In special cases refer to the I/O manual, the Vishay application notes, or contact directly Vishay Sales, Marketing or Application.

#### **MODE SWITCHING**

The TFDU6103 is in the SIR mode after power on as a default mode, therefore the FIR data transfer rate has to be set by a programming sequence using the TXD and SD inputs as described below. The low frequency mode covers speeds up to 115.2 kbit/s. Signals with higher data rates should be detected in the high frequency mode. Lower frequency data can also be received in the high frequency mode but with reduced sensitivity.

To switch the transceivers from low frequency mode to the high frequency mode and vice versa, the programming sequences described below are required.

### SETTING TO THE HIGH BANDWIDTH MODE (0.576 Mbit/s to 4 Mbit/s)

- 1. Set SD input to logic "high".
- 2. Set TXD input to logic "high". Wait  $t_s \ge 200$  ns.
- Set SD to logic "low" (this negative edge latches state of TXD, which determines speed setting).
- 4. After waiting  $t_h \ge 200$  ns TXD can be set to logic "low". The hold time of TXD is limited by the maximum allowed pulse length.

After that TXD is enabled as normal TXD input and the transceiver is set for the high bandwidth (576 kbit/s to 4 Mbit/s) mode.



### SETTING TO THE LOWER BANDWIDTH MODE (2.4 kbit/s to 115.2 kbit/s)

- 1. Set SD input to logic "high".
- 2. Set TXD input to logic "low". Wait  $t_s \ge 200 \text{ ns}$ .
- 3. Set SD to logic "low" (this negative edge latches state of TXD, which determines speed setting).
- 4. TXD must be held for  $t_h \ge 200$  ns.

After that TXD is enabled as normal TXD input and the transceiver is set for the lower bandwidth (9.6 kbit/s to 115.2 kbit/s) mode.

#### Note

When applying this sequence to the device already in the lower bandwidth mode, the SD pulse is interpreted as shutdown. In this case the RXD output of the transceiver may react with a single pulse (going active low) for a duration less than 2  $\mu s$ . The operating software should take care for this condition.

In case the applied SD pulse is longer than 4  $\mu s$ , no RXD pulse is to be expected but the receiver startup time is to be taken into account before the device is in receive condition.

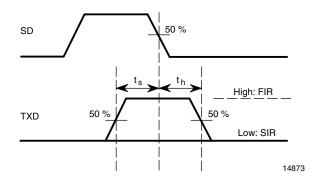


Fig. 2 - Mode Switching Timing Diagram

TABLE 2 - TRUTH TABLE									
		INPUTS	OUTPUTS	3					
SD TXD		OPTICAL INPUT IRRADIANCE mW/m <sup>2</sup>	RXD	TRANSMITTER					
High	х	x	Weakly pulled (500 k $\Omega$ ) to $V_{CC1}$	0					
	High	x	Low (active)	l <sub>e</sub>					
	High > 150 μs	x	High	0					
Low	Low	< 4	High	0					
23	Low	> min. irradiance E <sub>e</sub> < max. irradiance E <sub>e</sub>	Low (active)	0					
	Low	> max. irradiance E <sub>e</sub>	х	0					

#### **RECOMMENDED SOLDER PROFILES**

#### Solder Profile for Sn/Pb Soldering

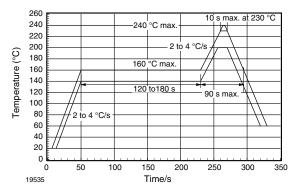


Fig. 3 - Recommended Solder Profile for Sn/Pb soldering

#### Lead (Pb)-free, Recommended Solder Profile

The TFDU6103 is a lead (Pb)-free transceiver and qualified for lead (Pb)-free processing. For lead (Pb)-free solder paste like Sn  $_{(3.0-4.0)}$  Ag  $_{(0.5-0.9)}$  Cu, there are two standard reflow profiles: Ramp-Soak-Spike (RSS) and Ramp-To-Spike (RTS). The Ramp-Soak-Spike profile was developed

primarily for reflow ovens heated by infrared radiation. With widespread use of forced convection reflow ovens the Ramp-To-Spike profile is used increasingly. Shown in figure 4 and 5 are Vishay's recommended profiles for use with the TFDU6103 transceivers. For more details please refer to the application note "SMD Assembly Instructions". A ramp-up rate less than 0.9 °C/s is not recommended. Ramp-up rates faster than 1.3 °C/s could damage an optical part because the thermal conductivity is less than compared

### to a standard IC. Wave Soldering

For TFDUxxxx and TFBSxxxx transceiver devices wave soldering is not recommended.

#### **Manual Soldering**

Manual soldering is the standard method for lab use. However, for a production process it cannot be recommended because the risk of damage is highly dependent on the experience of the operator. Nevertheless, we added a chapter to the above mentioned application note, describing manual soldering and desoldering.

# VISHAY.

### Vishay Semiconductors Fast Infrared Transceiver Module (FIR, 4 Mbit/s) for 2.4 V to 5.5 V Operation

#### **Storage**

The storage and drying processes for all Vishay transceivers (TFDUxxxx and TFBSxxx) are equivalent to MSL4. The data for the drying procedure is given on labels on the packing and also in the application note "Taping, Labeling, Storage and Packing".

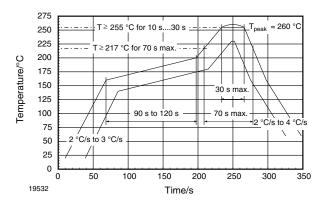


Fig. 4 - Solder Profile, RSS Recommendation

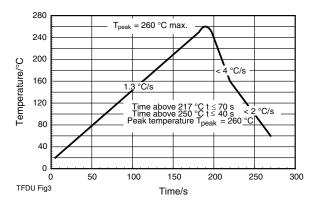


Fig. 5 - RTS Recommendation

#### **CURRENT DERATING DIAGRAM**

Figure 6 shows the maximum operating temperature when the device is operated without external current limiting resistor. A power dissipating resistor of 2  $\Omega$  is recommended from the cathode of the IRED to ground for supply voltages above 4 V. In that case the device can be operated up to 85  $^{\circ}\text{C}$ , too.

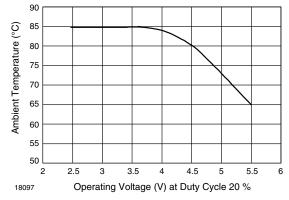


Fig. 6 - Temperature Derating Diagram



#### **PACKAGE DIMENSIONS** in millimeters

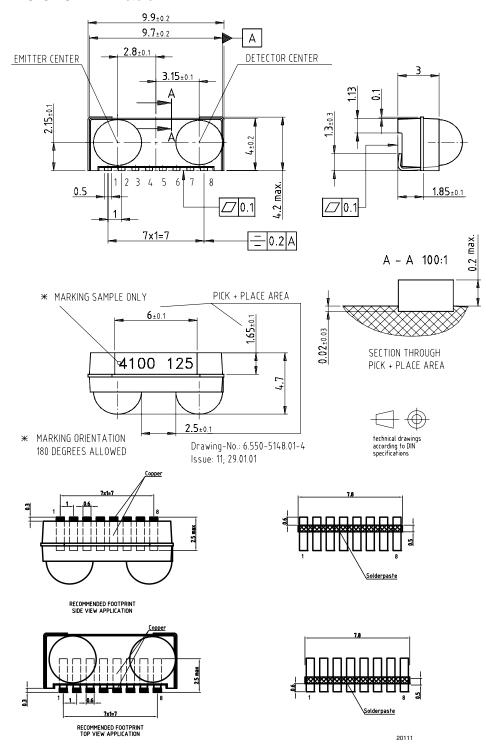
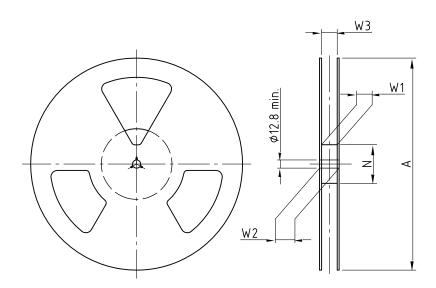


Fig. 7 - Package Drawing and Solder Footprints for Top and Side View Mounting TFDU6103, Tolerance ± 0.2 mm if not otherwise mentioned



#### **REEL DIMENSIONS** in millimeters



Reel hub 2:1

Drawing-No.: 9.800-5090.01-4 Issue: 1; 29.11.05

14017

Form of the leave open of the wheel is supplier specific.

Dimension acc. to IEC EN 60 286-3

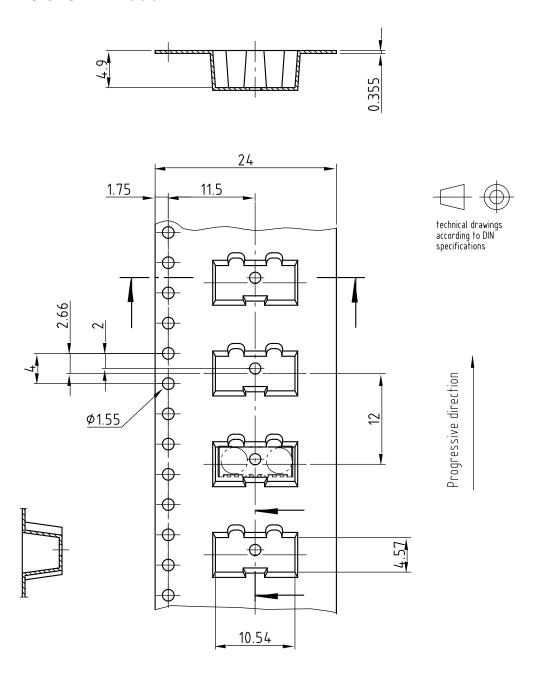


technical drawings according to DIN specifications

TAPE WIDTH (mm)	A MAX. (mm)	N (mm)	W <sub>1</sub> MIN. (mm)	W <sub>2</sub> MAX. (mm)	W <sub>3</sub> MIN. (mm)	W <sub>3</sub> MAX. (mm)
24	330	60	24.4	30.4	23.9	27.4



#### **TAPE DIMENSIONS** in millimeters



Drawing-No.: 9.700-5251.01-4

Issue: 3; 02.09.05

19824

Fig. 8 - Tape Drawing, TFDU6103 for Top View Mounting, Tolerance ± 0.1 mm



#### **TAPE DIMENSIONS** in millimeters

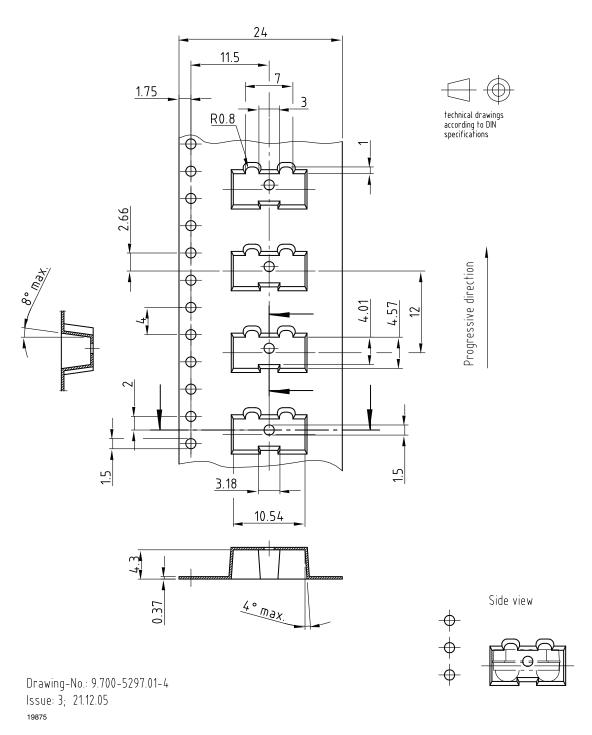


Fig. 9 - Tape Drawing, TFDU6103 for Side View Mounting, Tolerance  $\pm$  0.1 mm



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